

EN - For pricing and availability in your local country please visit one of the below links:

DE - Informationen zu Preisen und Verfügbarkeit in Ihrem Land erhalten Sie über die unten aufgeführten Links:

FR - Pour connaître les tarifs et la disponibilité dans votre pays, cliquez sur l'un des liens suivants:

[SLCD-61N8](#)

EN

This Datasheet is presented by
the manufacturer

DE

Dieses Datenblatt wird vom
Hersteller bereitgestellt

FR

Cette fiche technique est
présentée par le fabricant



SLCD-61N8

Solderable Planar Photodiode

Features

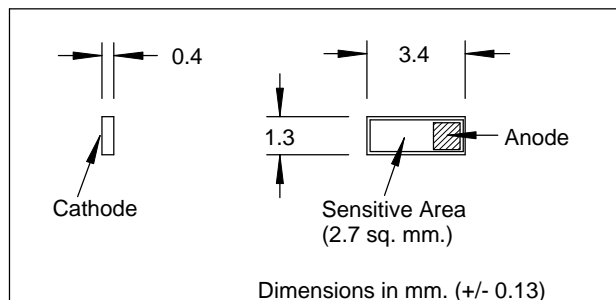
- Visible to IR spectral irradiance range
- High reliability
- Oxide passivation
- Linear short circuit current
- Low capacitance, high speed
- Available in arrays where # indicates number of elements (maximum of 8 elements)

Description

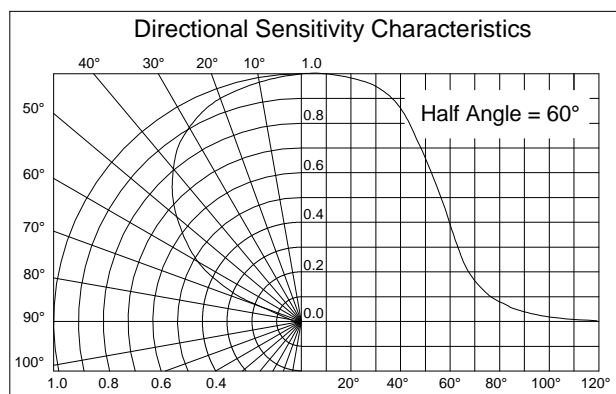
The Silonex series of silicon solderable planar photodiodes feature low cost, high reliability, and linear short circuit current over a wide range of illumination. These devices are widely used for light sensing and power generation because of their stability and high efficiency. They are particularly suited to power conversion applications due to their low internal impedance and relatively high shunt impedances, and stability. These devices also provide a reliable, inexpensive detector for applications such as light beam sensing and instrumentation. The electrical characteristics below are per element. In the multielement arrays the cathodes are common to a all elements.

Absolute Maximum Ratings

Storage Temperature	-40°C to +125°C
Operating Temperature	-40°C to +125°C



Also available with leads as part number SLSD-71N8



Electrical Characteristics (T_A=25°C unless otherwise noted)

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
I _{SC}	Short Circuit Current	100	170		μA	V _R =0V, E _e =25mW/cm ² (1)
V _{OC}	Open Circuit Voltage		0.40		V	E _e =25mw/cm ² (1)
I _D	Reverse Dark Current			1.7	μA	V _R =5V, E _e =0
C _J	Junction Capacitance		100		pF	V _R =0V, E _e =0, f=1MHz
S _λ	Spectral Sensitivity		0.55		A/W	λ=940nm
V _{BR}	Reverse Breakdown Voltage	20			V	I _R =100μA
λ _P	Maximum Sensitivity Wavelength		930		nm	
λ _R	Sensitivity Spectral Range	400		1100	nm	
θ _{1/2}	Acceptance Half Angle		60		deg	

Specifications subject to change without notice

104118 REV 0

Notes: (1) E_e = light source @ 2854 °K

EN - For pricing and availability in your local country please visit one of the below links:

DE - Informationen zu Preisen und Verfügbarkeit in Ihrem Land erhalten Sie über die unten aufgeführten Links:

FR - Pour connaître les tarifs et la disponibilité dans votre pays, cliquez sur l'un des liens suivants:

[SLCD-61N8](#)

EN

This Datasheet is presented by
the manufacturer

DE

Dieses Datenblatt wird vom
Hersteller bereitgestellt

FR

Cette fiche technique est
présentée par le fabricant